N-Channel Power MOSFET

250V, 22A, 60mΩ

FEATURES

- Low $R_{DS(ON)}$ 56mΩ (Typ.)
- Low gate charge typical @ 71nC (Typ.)
- Low C_{rss} typical @ 22pF (Typ.)
- RoHS compliant
- Halogen-free
- UL recognized file # E-326243
- Isolation voltage 2500V /1min.

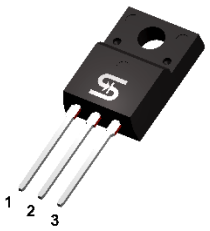
KEY PERFORMANCE PARAMETERS		
PARAMETER	**VALUE**	**UNIT**
V_{DS}	250	V
$R_{DS(on)}$ (max)	60	mΩ
Q_g	71	nC

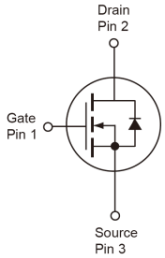
APPLICATIONS

- Uninterruptible power supply
- AC-DC power supply
- Lighting

Pb-Free RoHS COMPLIANT HALOGEN FREE

ITO-220TL





ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)				
PARAMETER		**SYMBOL**	**LIMIT**	**UNIT**
Drain-Source Voltage		V_{DS}	250	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current	T_C = 25°C	I_D	22	A
Pulsed Drain Current (Note 1)		I_{DM}	88	A
Total Power Dissipation @ T_C = 25°C		P_D	78	W
Single Pulse Avalanche Energy (Note 2)		E_{AS}	122	mJ
Single Pulse Avalanche Current (Note 2)		I_{AS}	28	A
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	°C

THERMAL PERFORMANCE			
PARAMETER	**SYMBOL**	**LIMIT**	**UNIT**
Junction to Case Thermal Resistance	$R_{\Theta JC}$	1.6	°C/W
Junction to Ambient Thermal Resistance (Note 3)	$R_{\Theta JA}$	65	°C/W

Notes:

1. Pulse Width ≤ 100μs.
2. L = 0.3mH, VGS = 20V, RG = 25Ω, Starting TJ = 25°C.
3. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta JA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)						
PARAMETER	**CONDITIONS**	**SYMBOL**	**MIN**	**TYP**	**MAX**	**UNIT**
Static (Note 4)						
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	BV_{DSS}	250	--	--	V
Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	$V_{GS(TH)}$	2	3.6	4.2	V
Gate Body Leakage	V_{GS} = ±30V, V_{DS} = 0V	I_{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V_{DS} = 250V, V_{GS} = 0V	I_{DSS}	--	--	1	μA
Drain-Source On-State Resistance	V_{GS} = 10V, I_D = 11A	$R_{DS(on)}$	--	56	60	mΩ
Forward Transconductance	V_{DS} = 10V, I_D = 2.5A	g_{fs}	--	9	--	S
Dynamic (Note 5)						
Total Gate Charge	V_{DS} = 125V, I_D = 3.6A, V_{GS} = 10V	Q_g	--	71	--	nC
Gate-Source Charge		Q_{gs}	--	16	--	
Gate-Drain Charge		Q_{gd}	--	26	--	
Input Capacitance	V_{DS} = 125V, V_{GS} = 0V, f = 1.0MHz	C_{iss}	--	3086	--	pF
Output Capacitance		C_{oss}	--	193	--	
Reverse Transfer Capacitance		C_{rss}	--	22	--	
Gate Resistance	f = 1.0MHz	R_g	--	3.6	--	Ω
Switching (Note 6)						
Turn-On Delay Time	V_{DD} = 125V, R_G = 3.3Ω, I_D = 3.6A, V_{GS} = 10V	$t_{d(on)}$	--	16	--	ns
Turn-On Rise Time		t_r	--	16	--	
Turn-Off Delay Time		$t_{d(off)}$	--	78	--	
Turn-Off Fall Time		t_f	--	25	--	
Source-Drain Diode						
Forward Voltage (Note 4)	I_S = 11A, V_{GS} = 0V	V_{SD}	--	0.8	1.4	V
Reverse Recovery Time	I_S = 3.6A, dI_F/dt = 100A/μs	t_{rr}	--	180	--	ns
Reverse Recovery Charge		Q_{rr}	--	1523	--	nC

Notes:

4. Pulse test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
5. Defined by design. Not subject to production test.
6. Switching time is essentially independent of operating temperature.

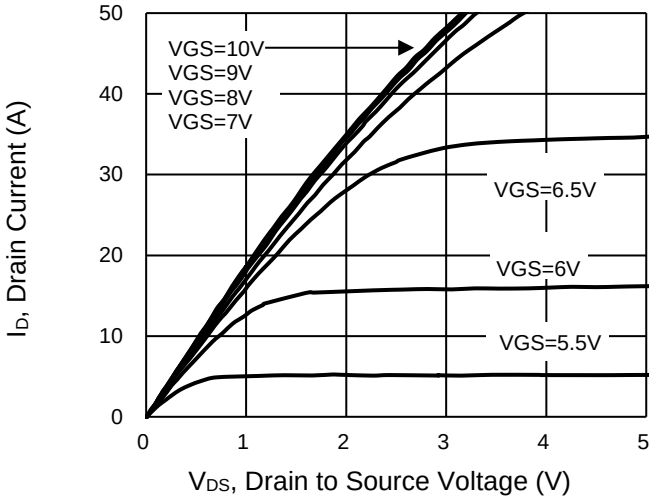
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM600NA25CIT C0G	ITO-220TL	50pcs / Tube

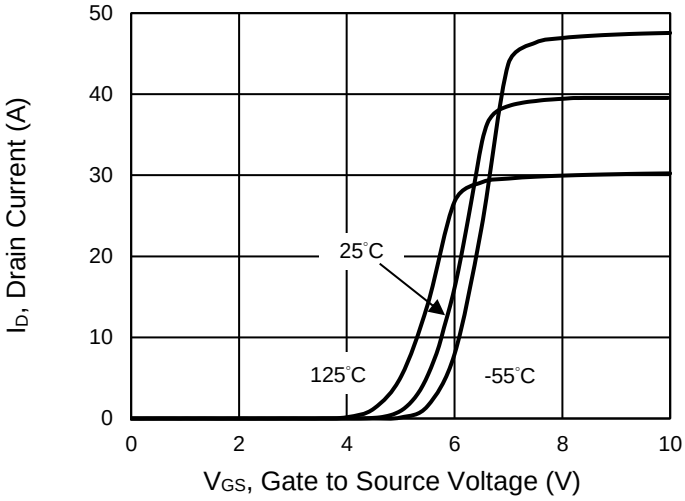
CHARACTERISTICS CURVES

(T_C = 25°C unless otherwise noted)

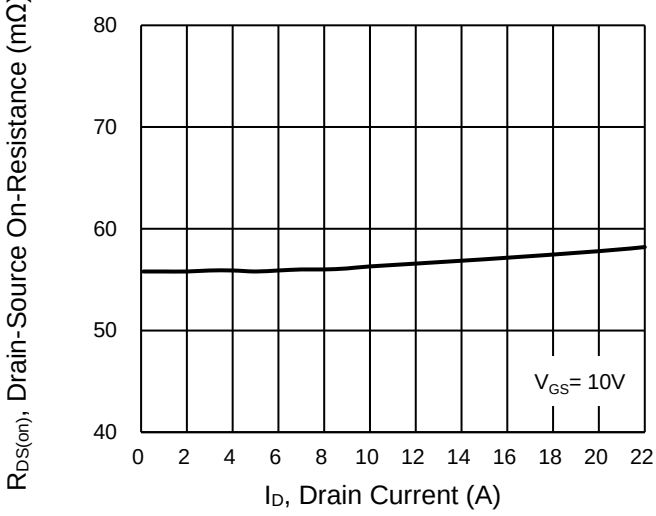
Output Characteristics



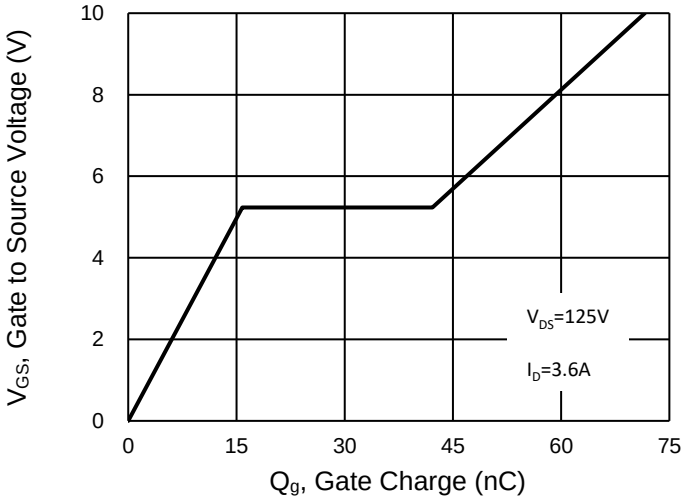
Transfer Characteristics



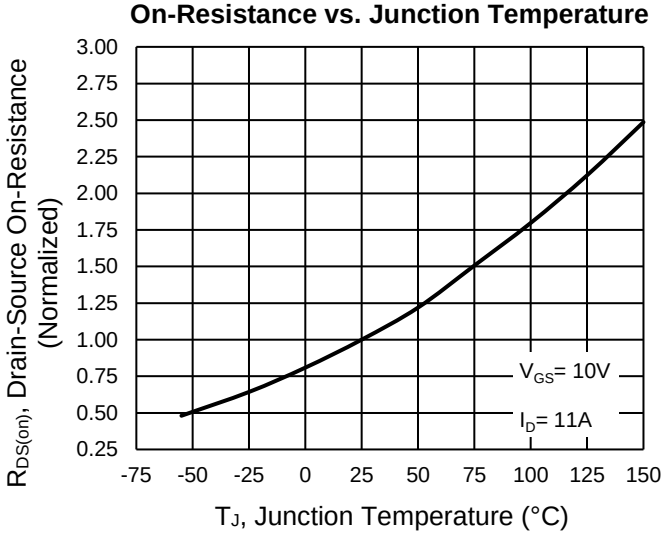
On-Resistance vs. Drain Current



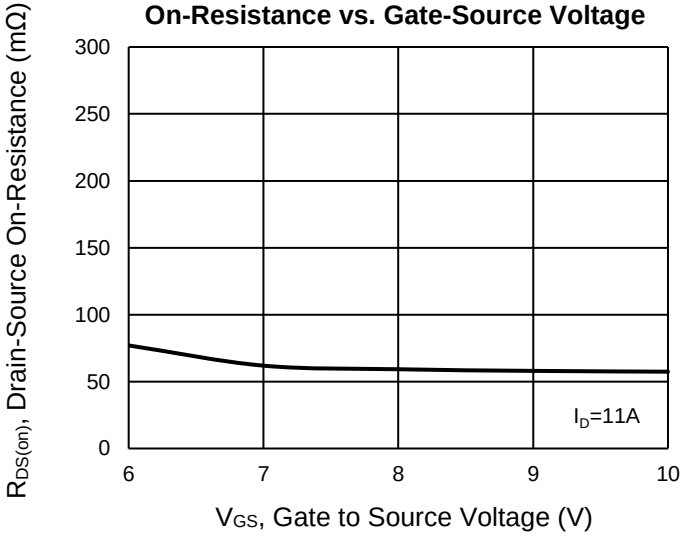
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



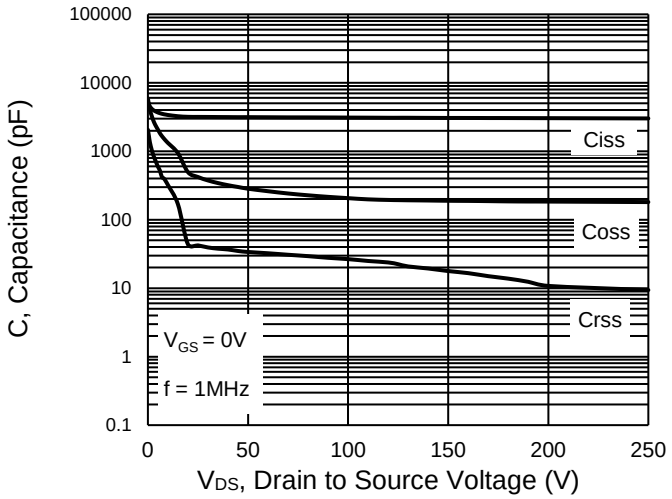
On-Resistance vs. Gate-Source Voltage



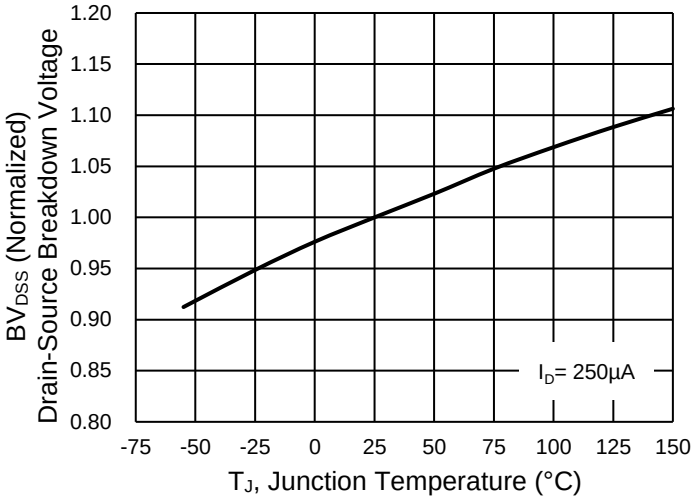
CHARACTERISTICS CURVES

(T_C = 25°C unless otherwise noted)

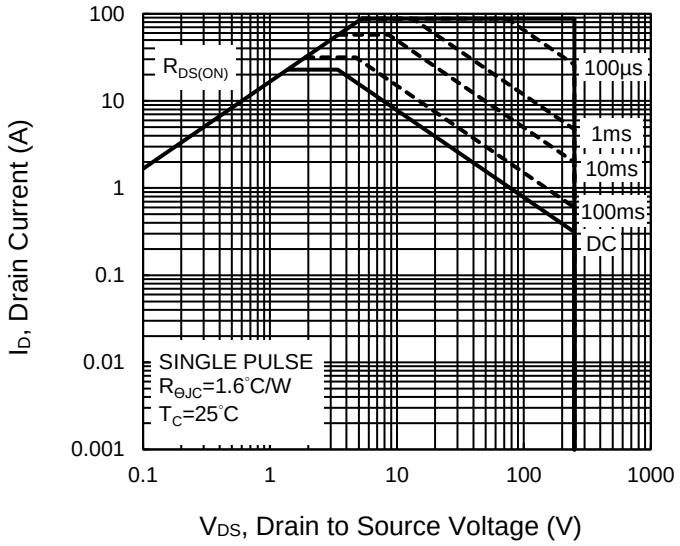
Capacitance vs. Drain-Source Voltage



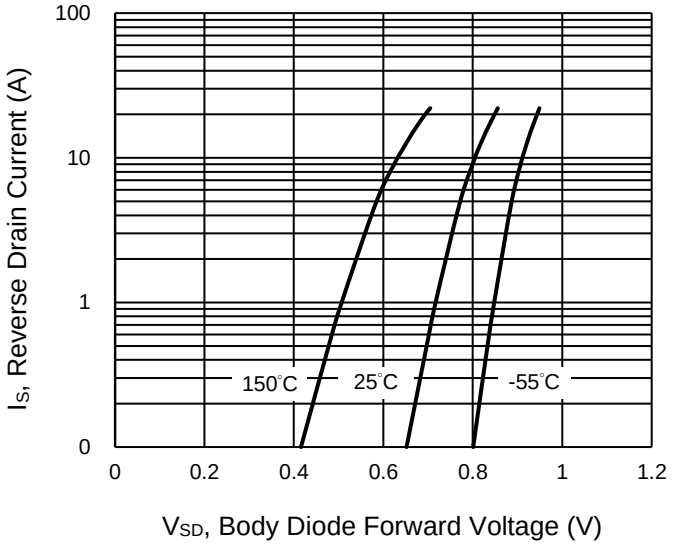
BV_{DSS} vs. Junction Temperature



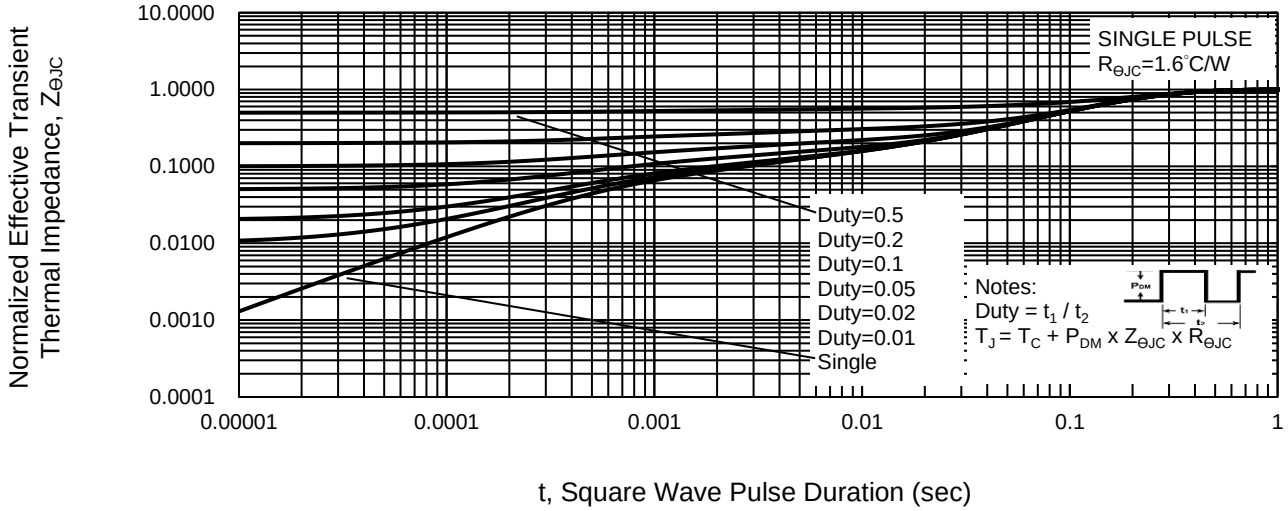
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage



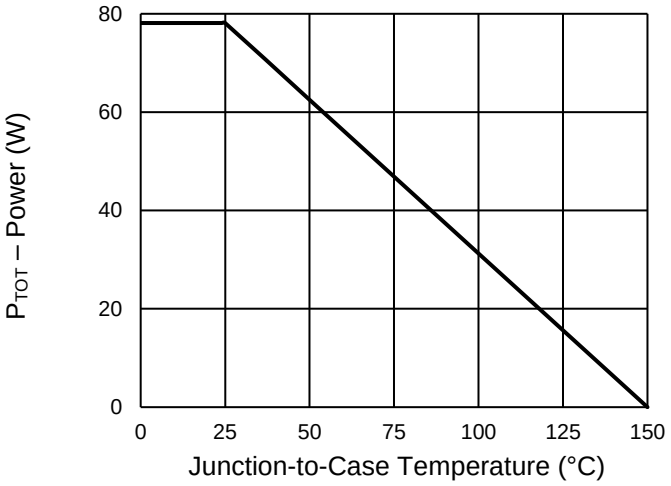
Normalized Thermal Transient Impedance, Junction-to-Case



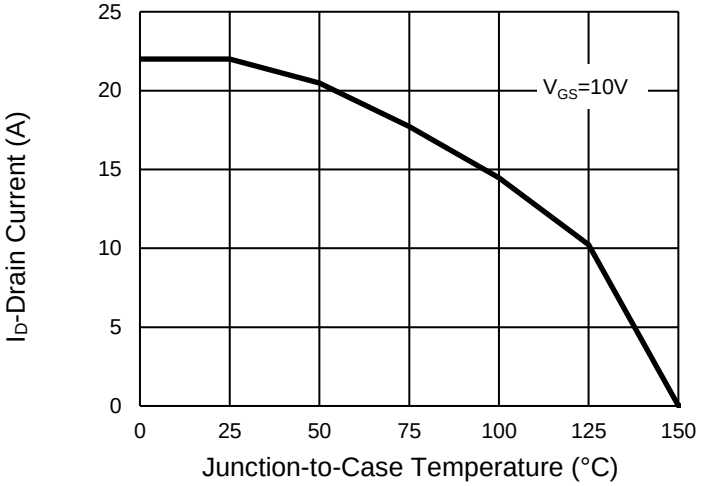
CHARACTERISTICS CURVES

(T_C = 25°C unless otherwise noted)

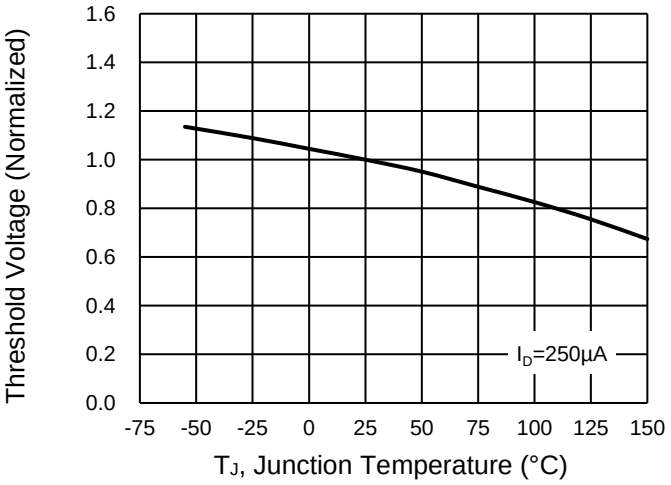
Power Dissipation



Drain Current

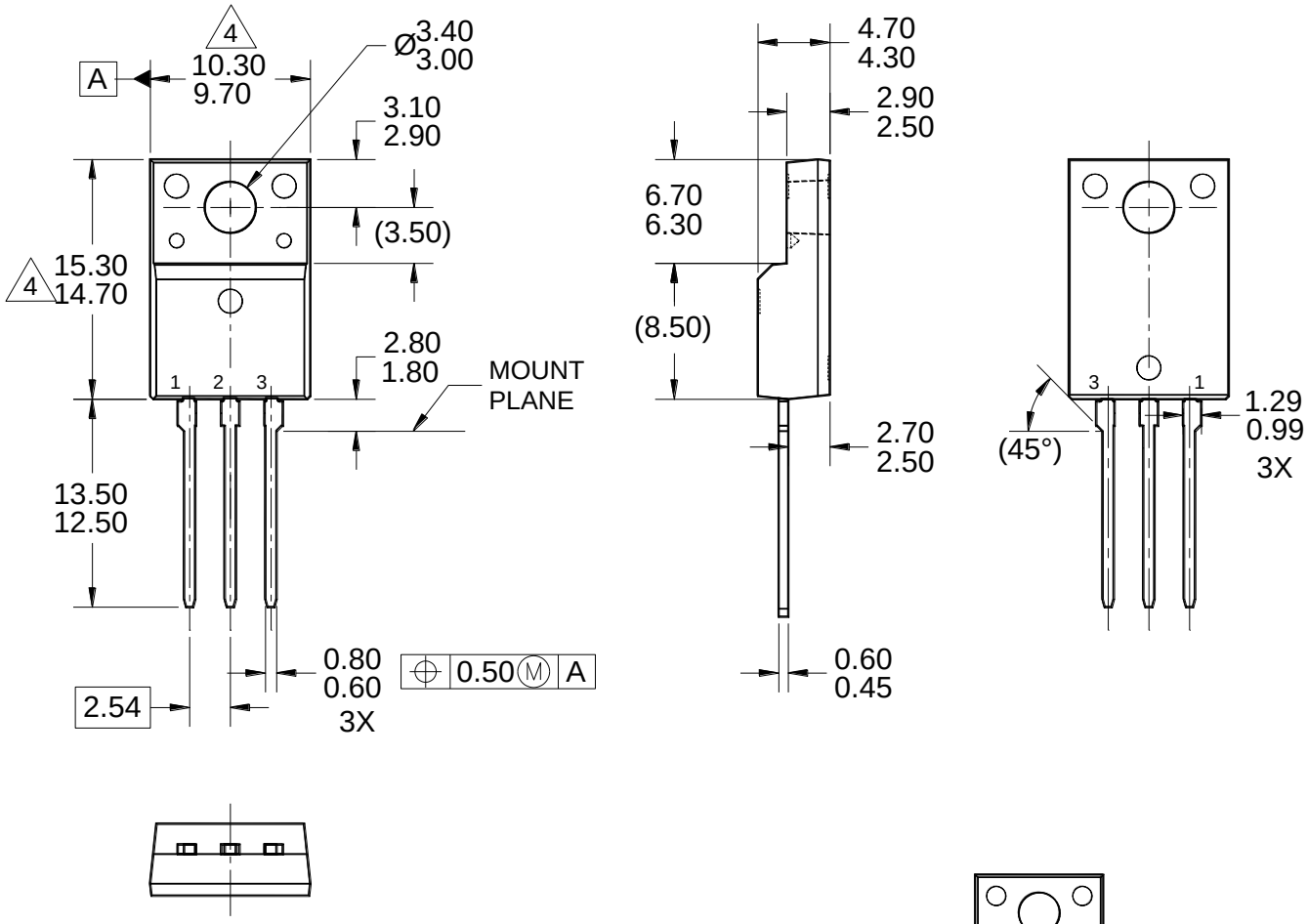


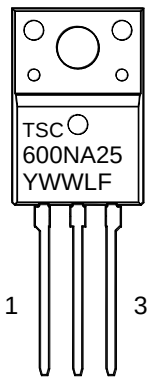
Normalized gate threshold voltage vs Temperature



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

ITO-220TL





MARKING DIAGRAM

NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PACKAGE OUTLINE REFERENCE: EIAJ ED-7500A-1, SC-91.
4. MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. DWG NO. REF: HQ2SD07-ITO220TL-016 REV B.

Y	= YEAR CODE
WW	= WEEK CODE (01~52)
L	= LOT CODE (1~9, A~Z)
F	= FACTORY CODE

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